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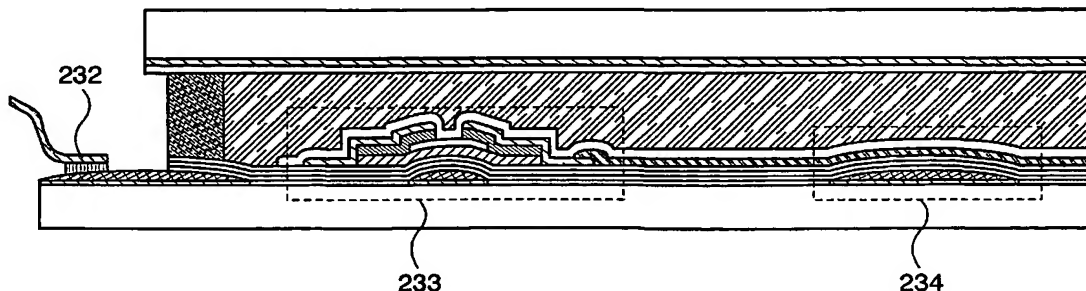
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(54) Title: LIQUID CRYSTAL DISPLAY DEVICE AND METHOD FOR MANUFACTURING THE SAME, AND LIQUID
CRYSTAL TELEVISION RECIEVER



(57) Abstract: At least one or more of a conductive layer which forms a wiring or an electrode and a pattern necessary for manu-
facturing a display panel such as a mask for forming a predetermined pattern is formed by a method capable of selectively forming
a pattern to manufacture a liquid crystal display device. A droplet discharge method capable of forming a predetermined pattern by
selectively discharging a droplet of a composition in accordance with a particular object is used as a method capable of selectively
forming a pattern in forming a conductive layer, an insulating layer, or the like.

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